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S/N 09/945535PATENTIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

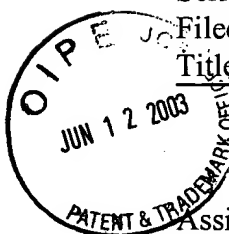
Examiner: David Blum

Serial No.: 09/945535

Group Art Unit: 2813

Filed: August 30, 2001

Docket: 1303.026US1

Title: HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO<sub>2</sub>**INFORMATION DISCLOSURE STATEMENT**

Assistant Commissioner for Patents

P.O.Box 1450

Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. § 1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER &amp; KLUTH, P.A.

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Reg. No. 47,857

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner of Patents, P.O.Box 1450, Alexandria, VA 22313-1450, on this 10th day of June, 2003

Name

Amy Morison

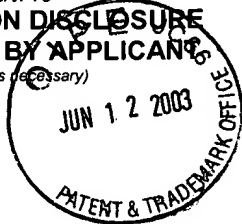
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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Application Number 09/945535

Filing Date August 30, 2001

First Named Inventor Ahn, Kie

Group Art Unit 2813

Examiner Name Blum, David

Sheet 1 of 3

Attorney Docket No: 1303.026US1

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**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
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	US-2002/0155688	10/24/2002	Ahn, K. Y., et al.	438	592	04/20/2001
	US-2002/0155689	10/24/2002	Ahn, K. Y., et al.	29	76	02/11/2002
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**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
	JP-2001-332546	11/30/2001		H01L	21/316	

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		International Technology for Semiconductor Roadmap, (1999),	
		BRIGHT, A A., et al., "Low-rate plasma oxidation of Si in a dilute oxygen/helium plasma for low-temperature gate quality Si/Sio2 interfaces", <u>Applied Physics Letters</u> , (February 1991), pp. 619-621	

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Examiner Name	Blum, David

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Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		CHENG, BAOHONG, et al., "The Impact of High-k Gate Dielectrics and Metal Gate Electrodes on Sub-100nm MOSFET's", <u>IEEE Transactions on Electron Devices</u> , (1999), pp. 1537-1544	
		FUYUKI, TAKASHI, et al., "Initial stage of ultra-thin SiO2 formation at low temperatures using activated oxygen", <u>Applied Surface Science</u> , (1997), pp. 123-126	
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Examiner Name	Blum, David

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		PAN, TUNG M., et al., "High-k cobalt-titanium oxide dielectrics formed by oxidation of sputtered Co/Ti or Ti/Co films", <u>Applied Physics Letters</u> , (March 2001), pp. 1439-1441	
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